

Advanced Product / Process Change Notice

Date: September 23, 2013.

No.: Z200-APCN-OM201309-01-P

Change Title: 1Gb (128Mb x8 and 64Mb x16) DDR2 technology migration from 65nm to 45nm Change item : ☑ Design ☐ Raw Material ☑ Wafer FAB ☐ Package Assembly ☐ Testing ☐ Others : Affected Product(s): W971GG6JB (64Mx16 DDR2 with 65nm technology) W971GG8JB (128Mx16 DDR2 with 65nm technology) Description of Change(s): (1) Technology migration (65nm → 45nm) for 1Gb DDR2 (2) New wafer manufacturing fab: Powerchip Semiconductor Corp. (Here-in-after: PSC, Address: No. 12, Li-Hsin Rd. 1, Hsinchu Science Park, Hsinchu, Taiwan) Reason for Change(s): According to Winbond product roadmap, launch new 1G DDR2 with 45nm technology Impact of Change(s): (positive & negative) Form: no change Fit: No change Function: No concern (fully compatible between 65nm and 45nm) Reliability: In progress Hazardous Substances: In progress Qualification Plan/ Results: (1) The qualification is in progress and expected come out in November/E/2013. (2) PSC is one company with TS16949 and OHSAS 18001 certificated company (Please refer to Attachment) Implementation Plan : □ Date Code : _____ onward □ Lot No.: _____ onward ☑ Proposed first ship date: <u>December/30/2013 (schedule)</u>. The follow-up disposition of 65nm 1Gb DDR2: 1) The date of Last-buy orders for the 65nm 1Gb DDR2: March. 31, 2014. 2) The last shipment date of the 65nm 1Gb DDR2: June.30, 2014. Approval: (QA Originator: (QA Approval: Yu-Sung, cheng ytt char Sec. Manager) Dept. Manager) (QRA Director) Name: <u>Hannah Cheng</u> TEL:<u>886-3-5678168</u> (ext.6553) FAX: <u>886-3-5796124</u> **Contact for Questions** Address: #539, Sec. 2, Wenxing Rd., Jhubei City, Hsinchu County 302, Taiwan & Concerns E-mail: yhcheng2@winbond.com



Customer Comments:

Note: Please sign this notice, and return to Winbond contact within **30** days. If no response is received within **30** days, this Change Request will be assumed to meet your approval.

■ Approval	■ Disapproval	□ Conditional Approval :
Comment:		
Data		
Date:		
Dept. name:		
Person in charge:		

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Table 1 The part no comparison table

Product	65nm Part No	45nm Part No
64Mx16 DDR2	W971GG6JB	W971GG6KB
128Mx8 DDR2	W971GG8JB	W971GG8KB